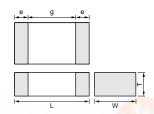
Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U) High Dielectric Constant Type 6.3/16/25/50V

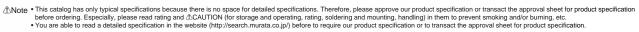




Part Number	Dimensions (mm)					
Part Number	L	W	T	е	g min.	
GRM155	1.0 ±0.05	0.5 ±0.05	0.5 ±0.05	0.15 to 0.3	0.4	
GRM188*	1.6 ±0.1	0.8 ±0.1	0.8 ±0.1	0.2 to 0.5	0.5	
GRM216	- 141		0.6 ±0.1			
GRM219	2.0 ±0.1	1.25 ±0.1	0.85 ±0.1	0.2 to 0.7	0.7	
GRM21B			1.25 ±0.1			
GRM319	2 2 40 15	1.6 ±0.15	0.85 ±0.1			
GRM31M	3.2 <u>£</u> 0.15	1.0 ±0.15	1.15 ±0.1	0.3 to 0.8	1.5	
GRM31C	3.2 ±0.2	1.6 ±0.2	1.6 ±0.2			

^{*} Bulk Case : 1.6 \pm 0.07(L) \times 0.8 \pm 0.07(W) \times 0.8 \pm 0.07(T)

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM155R61A683KA01	X5R (EIA)	10	68000pF±10%	1.0	0.5	0.50
GRM155R61A104KA01	X5R (EIA)	10	0.1μF±10%	1.0	0.5	0.50
GRM188R61A334KA61	X5R (EIA)	10	0.33 μF±10%	1.6	0.8	0.80
GRM188R61A474KA61	X5R (EIA)	10	0.47μF±10%	1.6	0.8	0.80
GRM188R61A684KA61	X5R (EIA)	10	0.68μF±10%	1.6	0.8	0.80
GRM188R61A105KA61	X5R (EIA)	10	1μF ±10%	1.6	0.8	0.80
GRM188R60J105KA01	X5R (EIA)	6.3	1μF ±10%	1.6	0.8	0.80
GRM219R61A105KC01	X5R (EIA)	10	1μF ±10%	2.0	1.25	0.90
GRM21BR61A225KA01	X5R (EIA)	10	2.2μF ±10%	2.0	1.25	1.25
GRM219R60J155KC01	X5R (EIA)	6.3	1.5μF ±10%	2.0	1.25	0.90
GRM21BR60J225KA01	X5R (EIA)	6.3	$2.2\mu F \pm 10\%$	2.0	1.25	1.25
GRM21BR60J335KA11	X5R (EIA)	6.3	$3.3\mu F \pm 10\%$	2.0	1.25	1.25
GRM21BR60J475KA11	X5R (EIA)	6.3	$4.7\mu F \pm 10\%$	2.0	1.25	1.25
GRM319R61A225KC01	X5R (EIA)	10	$2.2\mu F \pm 10\%$	3.2	1.6	0.90
GRM31XR61A335KC12	X5R (EIA)	10	$3.3\mu F \pm 10\%$	3.2	1.6	1.30
GRM31CR61A475KA01	X5R (EIA)	10	4.7μF ±10%	3.2	1.6	1.60
GRM31MR60J475KC11	X5R (EIA)	6.3	4.7μF ±10%	3.2	1.6	1.15
GRM31CR61A106KA01	X5R (EIA)	10	10μF ±10%	3.2	1.6	1.60
GRM31CR60J106KA01	X5R (EIA)	6.3	10μF ±10%	3.2	1.6	1.60
GRM31CR60J226ME20	X5R (EIA)	6.3	22μF ±20%	3.2	1.6	1.60
GRM32ER61A106KC01	X5R (EIA)	10	10μF ±10%	3.2	2.5	2.50
GRM55DR61H106KA01	X5R (EIA)	50	10μF ±10%	5.7	5.0	2.00
GRM15XR71H221KA86	X7R (EIA)	50	220pF±10%	1.0	0.5	0.25
GRM155R71H221KA01	X7R (EIA)	50	220pF±10%	1.0	0.5	0.50
GRM15XR71H331KA86	X7R (EIA)	50	330pF±10%	1.0	0.5	0.25
GRM155R71H331KA01	X7R (EIA)	50	330pF±10%	1.0	0.5	0.50
GRM15XR71H471KA86	X7R (EIA)	50	470pF±10%	1.0	0.5	0.25
GRM155R71H471KA01	X7R (EIA)	50	470pF±10%	1.0	0.5	0.50
GRM15XR71H681KA86	X7R (EIA)	50	680pF±10%	1.0	0.5	0.25
GRM155R71H681KA01	X7R (EIA)	50	680pF±10%	1.0	0.5	0.50
GRM15XR71H102KA86	X7R (EIA)	50	1000pF±10%	1.0	0.5	0.25
GRM155R71H102KA01	X7R (EIA)	50	1000pF±10%	1.0	0.5	0.50
GRM15XR71H152KA86	X7R (EIA)	50	1500pF±10%	1.0	0.5	0.25
GRM155R71H152KA01	X7R (EIA)	50	1500pF±10%	1.0	0.5	0.50
GRM155R71H222KA01	X7R (EIA)	50	2200pF±10%	1.0	0.5	0.50





Continued from the preceding page.

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness (mm)
RM155R71H332KA01	X7R (EIA)	50	3300pF±10%	1.0	0.5	0.50
RM155R71H472KA01	X7R (EIA)	50	4700pF±10%	1.0	0.5	0.50
GRM15XR71E182KA86	X7R (EIA)	25	1800pF±10%	1.0	0.5	0.25
GRM15XR71E222KA86	X7R (EIA)	25	2200pF±10%	1.0	0.5	0.25
GRM155R71E682KA01	X7R (EIA)	25	6800pF±10%	1.0	0.5	0.50
GRM155R71E103KA01	X7R (EIA)	25	10000pF±10%	1.0	0.5	0.50
GRM15XR71C332KA86	X7R (EIA)	16	3300pF±10%	1.0	0.5	0.25
GRM15XR71C472KA86	X7R (EIA)	16	4700pF±10%	1.0	0.5	0.25
GRM15XR71C682KA86	X7R (EIA)	16	6800pF±10%	1.0	0.5	0.25
GRM155R71C153KA01	X7R (EIA)	16	15000pF±10%	1.0	0.5	0.50
GRM155R71C223KA01	X7R (EIA)	16	22000pF±10%	1.0	0.5	0.50
GRM155R71A333KA01	X7R (EIA)	10	33000pF±10%	1.0	0.5	0.50
GRM155R71A473KA01	X7R (EIA)	10	47000pF±10%	1.0	0.5	0.50
GRM188R71H221KA01	X7R (EIA)	50	220pF±10%	1.6	0.8	0.80
GRM188R71H331KA01	X7R (EIA)	50	330pF±10%	1.6	0.8	0.80
GRM188R71H471KA01	X7R (EIA)	50	470pF±10%	1.6	0.8	0.80
GRM188R71H681KA01	X7R (EIA)	50	680pF±10%	1.6	0.8	0.80
GRM188R71H102KA01	X7R (EIA)	50	1000pF±10%	1.6	0.8	0.80
GRM188R71H152KA01	X7R (EIA)	50	1500pF±10%	1.6	0.8	0.80
GRM188R71H222KA01	X7R (EIA)	50	2200pF±10%	1.6	0.8	0.80
GRM188R71H332KA01	X7R (EIA)	50	3300pF±10%	1.6	0.8	0.80
GRM188R71H472KA01	X7R (EIA)	50	4700pF±10%	1.6	0.8	0.80
	X7R (EIA)	50	•	1.6	0.8	0.80
GRM188R71H682KA01			6800pF±10%			
GRM188R71H103KA01	X7R (EIA)	50	10000pF±10%	1.6	0.8	0.80
GRM188R71H153KA01	X7R (EIA)	50	15000pF±10%	1.6	0.8	0.80
GRM188R71H223KA01	X7R (EIA)	50	22000pF±10%	1.6	0.8	0.80
GRM188R71E333KA01	X7R (EIA)	25	33000pF±10%	1.6	0.8	0.80
GRM188R71E473KA01	X7R (EIA)	25	47000pF±10%	1.6	0.8	0.80
GRM188R71E683KA01	X7R (EIA)	25	68000pF±10%	1.6	0.8	0.80
GRM188R71E104KA01	X7R (EIA)	25	0.1μF±10%	1.6	0.8	0.80
GRM188R71C104KA01	X7R (EIA)	16	0.1μF±10%	1.6	0.8	0.80
GRM188R71A154KA01	X7R (EIA)	10	0.15μF±10%	1.6	0.8	0.80
GRM188R71A224KA01	X7R (EIA)	10	22000pF±10%	1.6	0.8	0.80
GRM219R71H333KA01	X7R (EIA)	50	33000pF±10%	2.0	1.25	0.90
GRM21BR71H473KA01	X7R (EIA)	50	47000pF±10%	2.0	1.25	1.25
GRM21BR71H683KA01	X7R (EIA)	50	68000pF±10%	2.0	1.25	1.25
GRM21BR71H104KA01	X7R (EIA)	50	0.1μF±10%	2.0	1.25	1.25
GRM21BR71H154KA01	X7R (EIA)	50	0.15μF±10%	2.0	1.25	1.25
GRM21BR71H224KA01	X7R (EIA)	50	22000pF±10%	2.0	1.25	1.25
GRM21BR71E104KA01	X7R (EIA)	25	$0.1\mu F \pm 10\%$	2.0	1.25	1.25
GRM21BR71E154KA01	X7R (EIA)	25	0.15μF±10%	2.0	1.25	1.25
GRM219R71E224KC01	X7R (EIA)	25	22000pF±10%	2.0	1.25	0.90
GRM21BR71E334KC01	X7R (EIA)	25	0.33 μF±10%	2.0	1.25	1.25
GRM21BR71E474KC01	X7R (EIA)	25	$0.47 \mu F \pm 10\%$	2.0	1.25	1.25
GRM219R71C474KC01	X7R (EIA)	16	$0.47 \mu F \pm 10\%$	2.0	1.25	0.90
GRM219R71C684KC01	X7R (EIA)	16	0.68μF±10%	2.0	1.25	0.90
GRM21BR71C105KA01	X7R (EIA)	16	1μF ±10%	2.0	1.25	1.25
GRM319R71H334KA01	X7R (EIA)	50	0.33 μF±10%	3.2	1.6	0.90
RM31MR71H474KA01	X7R (EIA)	50	0.47μF±10%	3.2	1.6	1.15
GRM319R71E684KC01	X7R (EIA)	25	0.68μF±10%	3.2	1.6	0.90
GRM31MR71E105KC01	X7R (EIA)	25	1μF ±10%	3.2	1.6	1.15
GRM319R71C105KC11	X7R (EIA)	16	1μF ±10%	3.2	1.6	0.90
GRM31MR71C155KC11	X7R (EIA)	16	1.5μF ±10%	3.2	1.6	1.15
GRM31MR71C225KA35	X7R (EIA)	16	2.2μF ±10%	3.2	1.6	1.15
GRM319R71A105KC01	X7R (EIA)	10	2.2μι ±10% 1μF ±10%	3.2	1.6	0.90

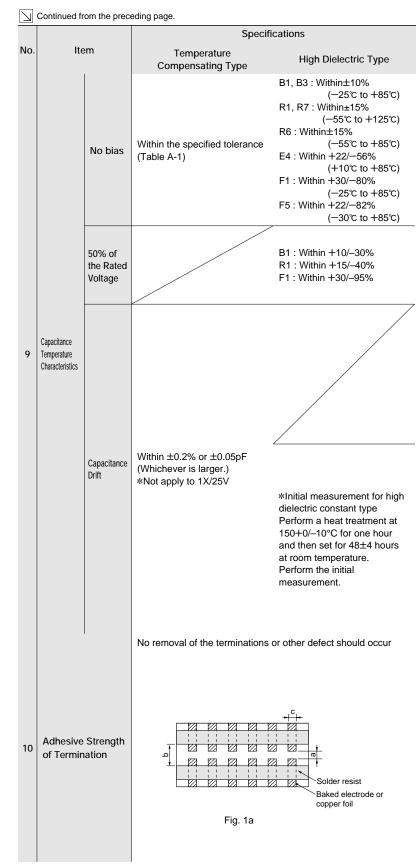
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Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM319R71A225KA01	X7R (EIA)	10	2.2μF ±10%	3.2	1.6	0.90
GRM32NR71H684KA01	X7R (EIA)	50	0.68μF±10%	3.2	2.5	1.35
GRM32RR71H105KA01	X7R (EIA)	50	1μF ±10%	3.2	2.5	1.80
GRM32RR71E225KC01	X7R (EIA)	25	2.2μF ±10%	3.2	2.5	1.80
GRM32MR71C225KC01	X7R (EIA)	16	2.2μF ±10%	3.2	2.5	1.15
GRM32NR71C335KC01	X7R (EIA)	16	3.3μF ±10%	3.2	2.5	1.35
GRM32RR71C475KC01	X7R (EIA)	16	4.7μF ±10%	3.2	2.5	1.80
GRM43ER71H225KA01	X7R (EIA)	50	2.2μF ±10%	4.5	3.2	2.50
GRM55RR71H105KA01	X7R (EIA)	50	1μF ±10%	5.7	5.0	1.80
GRM55RR71H155KA01	X7R (EIA)	50	1.5μF ±10%	5.7	5.0	1.80
GRM155F51H222ZA01	Y5V (EIA)	50	2200pF +80%, -20%	1.0	0.5	0.50
GRM155F51H472ZA01	Y5V (EIA)	50	4700pF +80%, -20%	1.0	0.5	0.50
GRM155F51H103ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.0	0.5	0.50
GRM155F51E223ZA01	Y5V (EIA)	25	22000pF +80%, -20%	1.0	0.5	0.50
GRM155F51C473ZA01	Y5V (EIA)	16	47000pF +80%, -20%	1.0	0.5	0.50
GRM155F51C104ZA01	Y5V (EIA)	16	10000pF +80%, -20%	1.0	0.5	0.50
GRM188F51H103ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H223ZA01	Y5V (EIA)	50	22000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H473ZA01	Y5V (EIA)	50	47000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H104ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.6	0.8	0.80
GRM188F51E104ZA01	Y5V (EIA)	25	10000pF +80%, -20%	1.6	0.8	0.80
GRM188F51C224ZA01	Y5V (EIA)	16	22000pF +80%, -20%	1.6	0.8	0.80
GRM188F51C474ZA01	Y5V (EIA)	16	0.47μF +80%, -20%	1.6	0.8	0.80
GRM188F51A474ZC01	Y5V (EIA)	10	0.47μF +80%, -20%	1.6	0.8	0.80
GRM188F51A105ZA01	Y5V (EIA)	10	1μF +80%, -20%	1.6	0.8	0.80
GRM219F51H104ZA01	Y5V (EIA)	50	10000pF +80%, -20%	2.0	1.25	0.90
GRM21BF51H224ZA01	Y5V (EIA)	50	22000pF +80%, -20%	2.0	1.25	1.25
GRM219F51E224ZA01	Y5V (EIA)	25	22000pF +80%, -20%	2.0	1.25	0.90
GRM21BF51E474ZA01	Y5V (EIA)	25	0.47μF +80%, -20%	2.0	1.25	1.25
GRM219F51E105ZA01	Y5V (EIA)	25	1μF +80%, -20%	2.0	1.25	0.90
GRM21BF51E225ZA01	Y5V (EIA)	25	2.2μF +80%, -20%	2.0	1.25	1.25
GRM219F51C105ZA01	Y5V (EIA)	16	1μF +80%, -20%	2.0	1.25	0.90
GRM21BF51C225ZA01	Y5V (EIA)	16	2.2μF +80%, -20%	2.0	1.25	1.25
GRM219F51A105ZA01	Y5V (EIA)	10	1μF +80%, -20%	2.0	1.25	0.90
GRM21BF51A225ZA01	Y5V (EIA)	10	2.2μF +80%, -20%	2.0	1.25	1.25
GRM21BF51A475ZA01	Y5V (EIA)	10	4.7μF +80%, -20%	2.0	1.25	1.25
GRM31MF51H474ZA01	Y5V (EIA)	50	0.47μF +80%, -20%	3.2	1.6	1.15
GRM31MF51E105ZA01	Y5V (EIA)	25	1μF +80%, -20%	3.2	1.6	1.15
GRM31MF51E475ZA01	Y5V (EIA)	25	4.7μF +80%, -20%	3.2	1.6	1.15
GRM319F51C105ZA01	Y5V (EIA)	16	1μF +80%, -20%	3.2	1.6	0.90
GRM31MF51C225ZA01	Y5V (EIA)	16	2.2μF +80%, -20%	3.2	1.6	1.15
GRM31MF51C475ZA12	Y5V (EIA)	16	4.7μF +80%, -20%	3.2	1.6	1.15
GRM319F51A225ZA01	Y5V (EIA)	10	2.2μF +80%, -20%	3.2	1.6	0.90
GRM31MF51A475ZA01	Y5V (EIA)	10	4.7μF +80%, -20%	3.2	1.6	1.15
GRM31MF51A106ZA01	Y5V (EIA)	10	10μF +80%, -20%	3.2	1.6	1.15
GRM31MF50J106ZA01	Y5V (EIA)	6.3	10μF +80%, -20%	3.2	1.6	1.15
GRM32RF51H105ZA01	Y5V (EIA)	50	1μF +80%, -20%	3.2	2.5	1.80
GRM329F51E475ZA01	Y5V (EIA)	25	4.7μF +80%, -20%	3.2	2.5	0.90
GRM32NF51E106ZA01	Y5V (EIA)	25	10μF +80%, -20%	3.2	2.5	1.35
GRM32NF51C106ZA01	Y5V (EIA)	16	10μF +80%, -20%	3.2	2.5	1.35
GRM188E41H103MA01	Z5U (EIA)	50	10000pF±20%	1.6	0.8	0.80
GRM188E41H223MA01	Z5U (EIA)	50	22000pF±20%	1.6	0.8	0.80
GRM216E41H473MA01	Z5U (EIA)	50	47000pF±20%	2.0	1.25	0.60
GRM219E41H104MA01	Z5U (EIA)	50	10000pF±20%	2.0	1.25	0.90
GRM319E41H224MA01	Z5U (EIA)	50	22000pF±20%	3.2	1.6	0.90

Note • This catalog has only typical specifications because there is no space for detailed specifications. Therefore, please approve our product specification or transact the approval sheet for product specification before ordering. Especially, please read rating and CAUTION (for storage and operating, rating, soldering and mounting, handling) in them to prevent smoking and/or burning, etc.
• You are able to read a detailed specification in the website (http://search.murata.co.jp/) before to require our product specification or to transact the approval sheet for product specification.

■ Specifications and Test Methods

		Specifi	cations	
No.	Item	Temperature Compensating Type	High Dielectric Type	Test Method
1	Operating Temperature Range	–55 to +125℃	B1, B3, F1: -25°C to +85°C R1, R7: -55°C to +125°C E4: +10°C to +85°C F5: -30°C to +85°C	Reference Temperature : 25°C (2Δ, 3Δ, 4Δ, B1, B3, F1, R1 : 20°C)
2	Rated Voltage	See the previous pages		The rated voltage is defined as the maximum voltage which may be applied continuously to the capacitor. When AC voltage is superimposed on DC voltage, V ^{p,p} or V ^{o,p} , whichever is larger, should be maintained within the rated voltage range.
3	Appearance	No defects or abnormalities		Visual inspection
4	Dimensions	Within the specified dimensions		Using calipers
5	Dielectric Strength	No defects or abnormalities		No failure should be observed when 300% of the rated voltage (temperature compensating type) or 250% of the rated voltage (high dielectric constant type) is applied between the terminations for 1 to 5 seconds, provided the charge/discharge current is less than 50mA.
6	Insulation Resistance	C≤0.047μF : More than 10,000l C>0.047μF : 500Ω • F	MΩ C : Nominal Capacitance	The insulation resistance should be measured with a DC voltage not exceeding the rated voltage at 20°C/25°C and 75%RH max. and within 2 minutes of charging, provided the charge/discharge current is less than 50mA.
7	Capacitance	Within the specified tolerance		The capacitance/D.F. should be measured at 20°C/25°C at the
8	Q/ Dissipation Factor (D.F.)	30pF and over : Q≥1000 30pF and below : Q≥400+20C C : Nominal Capacitance (pF)	[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.025max. W.V.: 16/10V: 0.035max. W.V.: 6.3V/4V : 0.05max. (C<3.3μF) : 0.1max. (C≧3.3μF) [F1, F5] W.V.: 25Vmin. : 0.05max. (C<0.1μF) : 0.09max. (C≥0.1μF) W.V.: 16V/10V: 0.125max. W.V.: 6.3V: 0.15max.	



Test Method

The capacitance change should be measured after 5min. at each specified temp. stage.

(1)Temperature Compensating Type

The temperature coefficient is determind using the capacitance measured in step 3 as a reference.

When cycling the temperature sequentially from step 1 through 5 (5C : +25°C to +125°C/ Δ C : +20°C to +125°C : other temp. coeffs. : +25°C to +85°C/+20°C to +85°C) the capacitance should be within the specified tolerance for the temperature coefficient and capacitance change as Table A-1.

The capacitance drift is caluculated by dividing the differences

between the maximum and minimum measured values in the step 1, 3 and 5 by the cap. value in step 3.

Step	Temperature (℃)
1	Reference Temperature±2
2	-55 ± 3 (for Δ C)/ -25 ± 3 (for other TC)
3	Reference Temperature±2
4	125 \pm 3 (for Δ C)/85 \pm 3 (for other TC)
5	Reference Temperature±2

(2) High Dielectric Constant Type

The ranges of capacitance change compared with the 20°C value over the temperature ranges shown in the table should be within the specified ranges.*

In case of applying voltage, the capacitance change should be measured after 1 more min. with applying voltage in equilibration of each temp. stage.

Step	Temperature (°C)	Applying Voltage (V)
1	Reference Tempereture±2	
2	-55±3 (for R1, R7, R6) -25±3 (for B1, B3, F1) -30±3 (for F5)/10±3 (for E4)	No bias
3	Reference Tempereture±2	INO DIAS
4	125±3 (for R1, R7)/ 85±3 (for B1, B3, R6 F1, F5, E4)	
5	Reference Tempereture±2	
6	−55±3 (for R1)/ −25±3 (for B1, F1)	50% of the rated
7	Reference Tempereture±2	voltage
8	125±3 (for R1)/ 85±3 (for B1, F1)	
	1 2 3 4 5 6	1 Reference Tempereture±2 -55±3 (for R1, R7, R6) -25±3 (for B1, B3, F1) -30±3 (for F5)/10±3 (for E4) 3 Reference Tempereture±2 125±3 (for R1, R7)/ 85±3 (for B1, B3, R6 F1, F5, E4) 5 Reference Tempereture±2 6 -55±3 (for R1)/ -25±3 (for B1, F1) 7 Reference Tempereture±2 8 125±3 (for R1)/

Solder the capacitor to the test jig (glass epoxy board) shown in Fig. 1a using an eutectic solder. Then apply 10N* force in parallel with the test jig for 10 ± 1 sec.

The soldering should be done either with an iron or using the reflow method and should be conducted with care so that the soldering is uniform and free of defects such as heat shock. *2N (GR \square 03), 5N (GR \square 15, GRM18)

			(in mm)
Туре	a	b	С
GR□03	0.3	0.9	0.3
GR□15	0.4	1.5	0.5
GRM18	1.0	3.0	1.2
GRM21	1.2	4.0	1.65
GRM31	2.2	5.0	2.0
GRM32	2.2	5.0	2.9
GRM43	3.5	7.0	3.7
GRM55	4.5	8.0	5.6

$\begin{tabular}{|c|c|c|c|}\hline \end{tabular}$ Continued from the preceding page.

			Specifi	cations				
No.	Ite	em	Temperature Compensating Type	High Dielectric Type	_	Test Me	ethod	
		Appearance Capacitance	No defects or abnormalities Within the specified tolerance					
11	Vibration Resistance	Q/D.F.	[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.025max. W.V.: 16/10V: 0.035max. W.V.: 6.3V/4V ∴ 0.05max. (C<3.3μF) ∴ 0.1max. (C≥3.3μF) [F1, F5] W.V.: 25Vmin. ∴ 0.05max. (C<0.1μF) ∴ 0.09max. (C≥0.1μF) W.V.: 16V/10V: 0.125max. W.V.: 6.3V: 0.15max. W.V.: 6.3V: 0.15max.			as (10). harmonic motion ncy being varied on and 55Hz. The to 10Hz, should motion should be		
			No crack or marked defect shou	uld occur	Solder the capacitor on the test jig (glass epoxy board) shown in Fig. 2a using an eutectic solder. Then apply a force in the direction shown in Fig. 3a for 5±1sec. The soldering should be done either with an iron or using the reflow method and should			
12	Defle	ction	R230 Capacitance in	Pressurizing speed: 1.0mm/sec. Pressurize Flexure : ≤1	Type GR□03 GR□15 GRM18 GRM21 GRM31 GRM32 GRM43 GRM55	a 0.3 0.4 1.0 1.2 2.2 2.2 3.5 4.5		C 0.3 0.5 1.2 1.65 2.0 2.9 3.7 5.6 (in mm)
13	Solderabi Terminati	•	75% of the terminations are to be continuously	,	Immerse the capa rosin (JIS-K-5902) Preheat at 80 to 1. After preheating, ii 2±0.5 seconds at	(25% rosin in v 20℃ for 10 to 3 mmerse in an e	weight propo 0 seconds.	ition) .
			The measured and observed ch specifications in the following ta	· · · · · · · · · · · · · · · · · · ·				
		Appearance Capacitance Change	No defects or abnormalities Within ±2.5% or ±0.25pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±7.5% F1, F5, E4 : Within ±20%	Preheat the capac Immerse the capa for 10±0.5 second	citor in an eute	ctic solder so	olution at 270±5℃
14	Resistance to Soldering Heat	Q/D.F.	30pF and over : Q≥1000 30pF and below : Q≥400+20C C : Nominal Capacitance (pF)	[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.025max. W.V.: 16/10V: 0.035max. W.V.: 6.3V/4V : 0.05max. (C<3.3μF) : 0.1max. (C≥3.3μF) [F1, F5] W.V.: 25Vmin. : 0.05max. (C<0.1μF) : 0.09max. (C≥0.1μF) W.V.: 16V/10V: 0.125max. W.V.: 6.3V: 0.15max.		pensating tyoe) on measure. ent for high dieleatment at 150+ emperature for measurement.	or 48±4 hou ectric consta -0/-10°C for 48±4 hours.	urs (high dielectric
		I.R. Dielectric Strength	More than 10,000M Ω or 500 Ω • No defects	e than 10,000MΩ or 500Ω • F (Whichever is smaller)				

\searrow	c

Continued from the preceding page.

		Specifi						
No. Ite	Item Temperature Compensating Type High Dielectric Type		High Dielectric Type	Test Method				
	The measured and observed characteristics should safisfy specifications in the following table							
	Appearance	No defects or abnormalities						
	Capacitance Change	Within ±2.5% or ±0.25pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±7.5% F1, F5, E4 : Within ±20%	Fix the capacitor to the supporting jig in the same manner and under the same conditions as (10). Perform the five cycles according to the four heat treatn shown in the following table.			atments	
			[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.025max. W.V.: 16/10V: 0.035max.	Set for 24±2 he hours (high die measure.	lectric constan	t type) at	room tempera	ture, ther
15 Temperature		30pF and over : Q≧1000	W.V.: 6.3V/4V	Step	1	2	3	4
Cycle	Q/D.F. 30pF and below : Q≥400+20C C : Nominal Capacitance (pF	30pF and below :	: 0.05max. (C<3.3µF) : 0.1max. (C≧3.3µF) [F1, F5]	Temp. (℃)	Min. Operating Temp.+0/-3	Room Temp.	Max. Operating Temp.+3/-0	Room Temp.
		C : Nominal Capacitance (pF)	W.V. : 25Vmin.	Time (min.)	30±3	2 to 3	30±3	2 to 3
			: 0.05max. (C<0.1μF) : 0.09max. (C≥0.1μF) W.V. : 16V/10V : 0.125max. W.V. : 6.3V : 0.15max.	•Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/−10℃ for one hour and then set at room temperature for 48±4 hours. Perform the initial measurement.				
	I.R.	More than $10,000M\Omega$ or 500Ω						
	Dielectric Strength	No defects						
		The measured and observed ch specifications in the following ta	•					
	Appearance	No defects or abnormalities						
	Capacitance Change	Within ±5% or ±0.5pF (Whichever is larger)	B1, B3, R1, R6, R7, C8 : Within ±12.5% F1, F5 : Within ±30%	_				
Humidity 16 (Steady State)	y 30pF and over : Q≥350 V 10pF and over V 30pF and below :		[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.05max. W.V.: 16/10V: 0.05max. W.V.: 6.3V/4V : 0.075max. (C<3.3μF) : 0.125max. (C≥3.3μF)	Set the capacitor at 40±2°C and in 90 to 95% humiduty for 500±12 hours. Remove and set for 24±2 hours (temperature compensatin type) or 48±4 hours (high dielectric constant type) at room temperature, then measure.				
	Q/D.F. 10pF and below: Q≥200+10C C : Nominal Capacitance (pF)	[F1, F5] W.V.: 25Vmin. : 0.075max. (C<0.1μF) : 0.125max. (C≧0.1μF) W.V.: 16V/10V: 0.15max. W.V.: 6.3V: 0.2max.						
	I.R.	More than $1,000M\Omega$ or $50\Omega \bullet F$	(Whichever is smaller)					

Continued from the preceding page.

		Specifications Temperature Compensating Type High Dielectric Type				
No.	Item			Test Method		
		The measured and observed chapecifications in the following ta	•			
	Appearance	No defects or abnormalities				
	Capacitance Change	Within ±7.5% or ±0.75pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±12.5% F1, F5, E4: Within ±30% [W.V.: 10Vmax.] F1, F5: Within +30/-40%	Apply the rated voltage at 40±2°C and 90 to 95% humidity for 500±12 hours. Remove and set for 24±2 hours (temperature		
17 Humid Load	Q/D.F.	30pF and over : Q≥200 30pF and below : Q≥100+10C/3 C : Nominal Capacitance (pF)	[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.05max. W.V.: 16/10V: 0.05max. W.V.: 6.3V : 0.075max. (C<3.3μF) : 0.125max. (C≥3.3μF) [F1, F5] W.V.: 25Vmin. : 0.075max. (C<0.1μF) : 0.125max. (C≥0.1μF) W.V.: 16V/10V: 0.15max. W.V.: 6.3V: 0.2max.	500±12 hours. Remove and set for 24±2 hours (temperat compensating type) or 48±4 hours (high dielectric constartype) at room temprature, then muasure. The charge/discrurrent is less than 50mA. •Initial measurement for F1, F5/10V max. Apply the rated DC voltage for 1 hour at 40±2°c. Remove and set for 48±4 hours at room temperature. Perform initial measurement.		
	I.R.	More than $500 \mathrm{M}\Omega$ or $25 \Omega \bullet \mathrm{F}$ (\	Whichever is smaller)			
		The measured and observed chapecifications in the following ta	-			
	Appearance	No defects or abnormalities				
	Capacitance Change	Within ±3% or ±0.3pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±12.5% F1, F5, E4 : Within ±30% [Exept 10Vmax. and. C≥1.0μF] F1, F5 : Within +30/−40% [10Vmax. and. C≥1.0μF]	Apply 200% of the rated voltage at the maximum operating temperature ±3°c for 1000±12 hours. Set for 24±2 hours (temperature compensating type) or 48±4 hours (high dielectric constant type) at room temperature, then measure.		
High 18 Temperat Load	Q/D.F.	30pF and over : Q≥350 10pF and over 30pF and below : Q≥275+2.5C 10pF and below : Q≥200+10C C : Nominal Capacitance (pF)	[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.04max. W.V.: 16/10V: 0.05max. W.V.: 6.3V : 0.075max.(C<3.3μF) : 0.125max.(C≥3.3μF) [F1, F5] W.V.: 25Vmin. : 0.075max.(C<0.1μF) : 0.125max.(C≥0.1μF) W.V.: 16V/10V: 0.15max. W.V.: 6.3V: 0.2max.	The charge/discharge current is less than 50mA. •Initial measurement for high dielectric constant type. Apply 200% of the rated DC voltage at the maximun operating temperature ±3℃ for one hour. Remove and set for 48±4 hours at room temperature. Perform initial measurement.		
	I.R.	More than 1,000M Ω or 50 Ω •F ((Whichever is smaller)			

 $\begin{tabular}{|c|c|c|c|}\hline \end{tabular}$ Continued from the preceding page.

Table A-1

· ,									
		Capacitance Change from 25°C (%)							
Char.	Nominal Values (ppm/℃)*1	-55		-30		-10			
		Max.	Min.	Max.	Min.	Max.	Min.		
5C	0± 30	0.58	-0.24	0.40	-0.17	0.25	-0.11		
6C	0± 60	0.87	-0.48	0.59	-0.33	0.38	-0.21		
6P	-150± 60	2.33	0.72	1.61	0.50	1.02	0.32		
6R	-220± 60	3.02	1.28	2.08	0.88	1.32	0.56		
6S	-330± 60	4.09	2.16	2.81	1.49	1.79	0.95		
6T	-470± 60	5.46	3.28	3.75	2.26	2.39	1.44		
7U	-750±120	8.78	5.04	6.04	3.47	3.84	2.21		
1X	+350 to -1000	_	_	_	_	_	_		

^{*1}Nominal values denote the temperature coefficient within a range of 25°C to 125°C (for ΔC)/85°C (for other TC).

			(Capacitance Cha	nge from 20℃ (%))	
Char.	Nominal Values (ppm/℃)*2	- 55		-2 5		-10	
	-	Max.	Min.	Max.	Min.	Max.	Min.
2C	0± 60	0.82	-0.45	0.49	-0.27	0.33	-0.18
3C	0±120	1.37	-0.90	0.82	-0.54	0.55	-0.36
4C	0±250	2.56	-1.88	1.54	-1.13	1.02	-0.75
2P	−150± 60	_	_	1.32	0.41	0.88	0.27
3P	-150±120	_	_	1.65	0.14	1.10	0.09
4P	-150±250	_	_	2.36	-0.45	1.57	-0.30
2R	-220± 60	_	_	1.70	0.72	1.13	0.48
3R	-220±120	_	_	2.03	0.45	1.35	0.30
4R	-220±250	_	_	2.74	-0.14	1.83	-0.09
2S	−330± 60	_	_	2.30	1.22	1.54	0.81
3S	-330±120	_	_	2.63	0.95	1.76	0.63
4S	-330±250	_	_	3.35	0.36	2.23	0.24
2T	-470 ± 60	_	_	3.07	1.85	2.05	1.23
3T	-470±120	_	_	3.40	1.58	2.27	1.05
4T	-470±250	_	_	4.12	0.99	2.74	0.66
3U	-750±120	_	_	4.94	2.84	3.29	1.89
4U	-750±250	_	_	5.65	2.25	3.77	1.50

^{*2}Nominal values denote the temperature coefficient within a range of 20°C to 125°C (for ΔC)/85°C (for other TC).



Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U)

High Dielectric Constant Type 100V

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM188R72A222KD01	X7R (EIA)	100	2200pF±10%	1.6	0.8	0.80
GRM188R72A332KD01	X7R (EIA)	100	3300pF±10%	1.6	0.8	0.80
GRM219R72A472KA01	X7R (EIA)	100	4700pF±10%	2.0	1.25	0.90
GRM219R72A682KA01	X7R (EIA)	100	6800pF±10%	2.0	1.25	0.90
GRM21BR72A103KA01	X7R (EIA)	100	10000pF±10%	2.0	1.25	1.25
GRM31MR72A333KA01	X7R (EIA)	100	33000pF±10%	3.2	1.6	1.15
GRM31MR72A473KA01	X7R (EIA)	100	47000pF±10%	3.2	1.6	1.15
GRM32NR72A683KA01	X7R (EIA)	100	68000pF±10%	3.2	2.5	1.35
GRM32NR72A104KA01	X7R (EIA)	100	0.1μF±10%	3.2	2.5	1.35
GRM43RR72A154KA01	X7R (EIA)	100	0.15μF±10%	4.5	3.2	1.80
GRM43RR72A224KA01	X7R (EIA)	100	22000pF±10%	4.5	3.2	1.80
GRM43DR72A474KA01	X7R (EIA)	100	0.47μF±10%	4.5	3.2	2.00
GRM55DR72A105KA01	X7R (EIA)	100	1μF ±10%	5.7	5.0	2.00
GRM188F52A472ZD01	Y5V (EIA)	100	4700pF +80%, -20%	1.6	0.8	0.80
GRM32NF52A104ZA01	Y5V (EIA)	100	10000pF +80%, -20%	3.2	2.5	1.35
GRM55RF52A474ZA01	Y5V (EIA)	100	0.47μF +80%, -20%	5.7	5.0	1.80

Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U)

			. ,			
Part Number			nsions (mi			
T dit Number	L	W	T	e min.	g min.	-
GRM033	0.6 ±0.03	0.3 ±0.03	0.3 ±0.03	0.1 to 0.2	0.2	S
GRM155	1.0 ±0.05	0.5 ±0.05	0.5 ±0.05	0.15 to 0.3	0.4	2 2 2 2 2
GRM185	1.6 ±0.1	0.8 ±0.1	0.5 +0/-0.2	0.2 to 0.5	0.5	
GRM188	1.6 ±0.1	0.8 ±0.1	0.8 ± 0.1	0.2 to 0.5	0.5	
GRM216			0.6 ±0.1			
GRM219	2.0 ±0.1	1.25 ±0.1	0.85 ±0.1	0.2 to 0.7	0.7	
GRM21B			1.25 ±0.1			
GRM316			0.6 ±0.1			
GRM319	3.2 ±0.15	1.6 ±0.15	0.85 ±0.1	0.3 to 0.8	1.5	e g e
GRM31M	1		1.15 ±0.1	0.3 10 0.6	1.5	
GRM31C	3.2 ±0.2	1.6 ±0.2	1.6 ±0.2			
GRM32D	3.2 ±0.3	2.5 ±0.2	2.0 ±0.2	0.3	1.0	
GRM32E	3.2 ±0.3	2.5 ±0.2	2.5 ±0.2	0.3	1.0	
GRM43D			2.0 ±0.2			T_
GRM43E	4.5 ±0.4	3.2 ±0.3	2.5 ±0.2	0.3	2.0	<u> </u>
GRM43S]		2.8 ±0.2			L W
GRM55F	5.7 ±0.4	5.0 ±0.4	3.2 ±0.2	0.3	2.0	

0.2 0.4 0.5 0.5	
0.7	
1.5	e g e
1.0	
2.0	
2.0	L W

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM155R60J154KE01	X5R (EIA)	6.3	0.15μF±10%	1.0	0.5	0.50
GRM155R60J224KE01	X5R (EIA)	6.3	22000pF±10%	1.0	0.5	0.50
GRM155R60J334KE01	X5R (EIA)	6.3	0.33 μF±10%	1.0	0.5	0.50
GRM155R60J474KE19	X5R (EIA)	6.3	0.47μF±10%	1.0	0.5	0.50
GRM188R60J225KE01	X5R (EIA)	6.3	2.2μF ±10%	1.6	0.8	0.80
GRM219R60J475KE01	X5R (EIA)	6.3	4.7μF ±10%	2.0	1.25	0.90
GRM21BR60J106KE01	X5R (EIA)	6.3	10μF ±10%	2.0	1.25	1.25
GRM21BR60J106ME01	X5R (EIA)	6.3	10μF ±20%	2.0	1.25	1.25
GRM32DR60J226KA01	X5R (EIA)	6.3	22μF ±10%	3.2	2.5	2.00
GRM32ER60J476ME20	X5R (EIA)	6.3	47μF ±20%	3.2	2.5	2.50
GRM43SR60J107ME20	X5R (EIA)	6.3	100μF ±20%	4.5	3.2	2.80
GRM55FR60J107KA01	X5R (EIA)	6.3	100μF ±10%	5.7	5.0	3.20
GRM55FR60J107MA01	X5R (EIA)	6.3	100μF ±20%	5.7	5.0	3.20
GRM21BF50J106ZE01	Y5V (EIA)	6.3	10μF +80%, -20%	2.0	1.25	1.25

No.	Ite	em	Specifications	Test Method				
1	Operating Temperat Range		B1, B3, F1: -25°C to +85°C R6: -55°C to +85°C F5: -30°C to +85°C C8: -55°C to +105°C, C7: -55°C to +125°C	Reference Temperature : 25°C (B1, B3, F1 : 20°C)				
2	2 Rated Voltage		See the previous pages	The rated voltage is defined as the maximum voltage which may be applied continuously to the capacitor. When AC voltage is superimposed on DC voltage, V ^{p,p} or V ^{o,p} , whichever is larger, should be maintained within the rated voltage range.				
3	Appearar	nce	No defects or abnormalities	Visual insp	ection			
4	Dimensio	ns	Within the specified dimensions	Using calip	ers			
5	Dielectric	Strength	No defects or abnormalities	is applied l	should be observe between the termi ne charge/dischar	nations for 1 t		
6	Insulation Resistant		More than 50Ω ∙ F	not exceed 75%RH ma		ge at Referen		
			Within the specified tolerance	The capac	itance should be r	measured at F	Reference	
							shown in the table.	
			*Table 1		apacitance	Frequency	Voltage	
7	Capacita	nce	GRM155 B3/R6 1A 124 to 224		μF (10V min.)*1 μF (6.3V max.)	1±0.1kHz 1±0.1kHz	1.0±0.2Vrms 0.5±0.1Vrms	
	очриони		GRM185 B3/R6 1A 105	C>10		120±24Hz	0.5±0.1Vrms	
			GRM188 B3/R6 1C/1A 225 GRM219 B3/R6 1A 475					
			GRM217 B3/R6 1C/1A 106		wever the Voltage ns on the left side		Vrms about Table 1	
			<u> </u>	iter	ns on the left side	-		
			B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.2 max.		hould be measure and voltage show		ce Temperature at the	
					and voltage show		Voltage	
			*Table 1		μF (10V min.)*1	Frequency 1±0.1kHz	1.0±0.2Vrms	
8	•	on Factor	GRM155 B3/R6 1A 124 to 224		μF (6.3V max.)	1±0.1kHz	0.5±0.1Vrms	
	(D.F.)		GRM185 B3/R6 1A 105 GRM188 B3/R6 1C/1A 225	C>10		120±24Hz	0.5±0.1Vrms	
			GRM219 B3/R6 1A 475 *1 However the Voltage is 0.5+/-0.1				Vrms shout Table 1	
			GRM21B B3/R6 1C/1A 106		ns on the left side		viilis about Table T	
				•	itance change sho	ould be measu	ured after 5min. at	
			B1, B3 : Within +/−10% (−25°C to +85°C)		s of capacitance o	hange compa	red with the	
			F1 : Within +30/−80% (−25°C to +85°C)	Reference Temperature value over the temperature ranges				
		No bias	R6 : Within +/−15% (−55°C to +85°C)		ne table should be		•	
			F5 : Within +22/-82% (-30°C to +85°C) In case of applying Voltage, the capaci				•	
			C7 : Within +/−22% (−55°C to +125°C) C8 : Within +/−22% (−55°C to +105°C)		on of each temp. s		voitage in	
				oquiiibratio	m or odon tomp. o	nago.		
				*GRM43 E	31/R6 0J/1A 336/4	476 only : 1.0±	E0.2Vrms	
				Step	Temperatur	e (°C)	Applying Voltage (V)	
				1	Reference Tem	pereture±2		
9	Capacitance Temperature			2	-55±3 (for R6 -25±3 (for B -30±3 (for	1, B3, F1)		
	Characteristics			3	Reference Tem		No bias	
					85±3 (for B1, B3	-		
		50% of the Rated	B1: Within +10/-30%	4	125±3 (fc 105±3 (fc	or C7)/		
		Voltage	F1: Within +30/—95%	5	20±	2		
		3		6	−25±3 (for	B1, F1)	50% of the rated	
				7	20±	-	voltage	
				8	85±3 (for I		renage	
						. ,	netant typo	
					asurement for high heat treatment at		C for one hour and	
					r 48±4 hours at ro			
					e initial measuren	•		

Solderability of Termination

lo.	Item	Specifications		Test M	ethod	
		No removal of the terminations or other defects should occur	Solder the capacit in Fig. 1a using ar parallel with the te The soldering sho reflow method and soldering is uniforn *5N: GR□15/GR	eutectic solde st jig for 10+/- uld be done eit I should be cor m and free of c	er. Then apply of the control of the	10N* force in n or using the are so that the
	Adhesive Strength		Туре	а	b	С
0	of Termination		GR□03	0.3	0.9	0.3
	or remination		GR□15	0.4	1.5	0.5
		Solder resist	GRM18	1.0	3.0	1.2
		Baked electrode or	GRM21	1.2	4.0	1.65
		copper foil	GRM31	2.2	5.0	2.0
			GRM32	2.2	5.0	2.9
		Fig. 1a	GRM43	3.5	7.0	3.7
			GRM55	4.5	8.0	5.6
	Appearance Capacitance	No defects or abnormalities Within the specified tolerance	Solder the capacit same manner and The capacitor sho	under the san	ne conditions a ed to a simple h	s (10). narmonic mot
11 Vibra	Vibration D.F.	B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.2 max.	having a total ampuniformly between frequency range, to be traversed in apapplied for a periodirections (total of	the approximation 10 to 55H proximately 1 indicates the second of 2 hours in	ate limits of 10 z and return to minute. This m	and 55Hz. Th 10Hz, should otion should b
		No cracking or marking defects should occur	Solder the capacit in Fig. 2a using ar direction shown in be done either wit should be conduct and free of defects	eutectic solde Fig. 3a for 5+ h an iron or us ted with care s	er. Then apply a /—1 sec. The s ing the reflow r o that the solde	a force in the oldering shound and
		50 Pressunzing speed: 1.0mm/sec.		b ►	ø4.5	
		Pressunze R230 Flexure : ≤1		† c	04	
	D (1	Capacitance meter		100	7	t : 1.6mm
2	Deflection	45 45		Fig. 2		
						!□15 : t : 0.8mm)
		Fig. 25	Type	а	b	С
		Fig.3a	GR□03	0.3	0.9	0.3
			GR□15	0.4	1.5	0.5
			GRM18	1.0	3.0	1.2
			GRM21	1.2	4.0	1.65
			GRM31	2.2	5.0	2.0
			GRM32	2.2	5.0	2.9
			GRM43	3.5	7.0	3.7
			GRM55	4.5	8.0	5.6
			GIGINIO	1.0	. 0.0	(in mm
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Continued on the following page.

Preheat at 80 to 120°C for 10 to 30 seconds.

After preheating, immerse in an eutectic solder solution for 2+/-0.5 seconds at 230+/-5°C.

continuously

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No.	Ite	Item Specifications Test Method							
14	Resistance to Soldering Heat	Note than 5022 • F		Preheat the capacitor at 120 to 150°C for 1 minute. Immerse the capacitor in an eutectic solder solution at 270+/-5°C for 10+/-0.5 seconds. Set at room temperature for 24+/-2 hours (temperature compensating tyoe) or 48+/-4 hours (high dielectric constant type), then measure. •Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10°C for one hour and					
		Strength	No defects	Perform the in	1 100°C to 120°C 1 min.				
	Temperature Sudden	Appearance Capacitance Change D.F.	No defects or abnormalities B1, B3, R6, C7, C8: Within ±7.5% F1, F5: Within ±20% B1, B3, R6, C7, C8: 0.1 max. F1, F5: 0.2 max. More than 50Ω • F	under the sam Perform the five shown in the five Set for 24+/	ne conditions a ve cycles acco following table. 2 hours (tempe s (high dielectri	es (10). ording to the erature control	in the same me he four heat tre compensating ty nt type) at roon	eatments /pe) or	
15		Dielectric	No defects	Step	1	2	3	4	
15	Change	Strength		Time (min.) •Initial measur Perform a hea then set at roo	•	150+0/- e for 48+/	Max. Operating Temp. +3/-0 30±3 c constant type 10°C for one hc /-4 hours.		
16	High Temperature High Humidity (Steady)	Appearance Capacitance Change D.F. I.R.	No defects or abnormalities B1, B3, R6, C7, C8 : Within $\pm 12.5\%$ F1, F5 : Within $\pm 30\%$ B1, B3, R6, C7, C8 : 0.2 max. F1, F5 : 0.4 max. More than $12.5\Omega \bullet F$	Apply the rate 500+/-12 hou 50mA. Initial measure then let sit for initial measure	d voltage at 40 urs. The charge rement at treatment at 48+/–4 hours ement.	0+/−2℃ a e/dischar 150+0/−	ind 90 to 95% I ge currentis les 10°C for one ho temperature. P	ss than	
		Appearance Capacitance Change D.F.	No defects or abnormalities B1, B3, R6, C7, C8: Within ±12.5% F1, F5: Within ±30% B1, B3, R6, C7, C8: 0.1 max. F1, F5: 0.4 max.	then let sit for measure. Apply 150% of maximum ope hours at room The charge/ di	•Measurement after test Perform a heat treatment at 150+0/−10℃ for one hear then let sit for 48+/−4 hours at room temperature, measure. Apply 150% of the rated voltage for 1000+/−12 homaximum operating temperature +/−3℃. Let sit for hours at room temperature, then measure. The charge/ discharge current is less than 50mA. •Initial measurement				
17	Durability	I.R.	More than 25Ω • F	then let sit for initial measure •Measuremen Perform a hea	48+/-4 hours ement. It after test at treatment at	at room to	10°C for one ho temperature. P 10°C for one ho temperature, th	erform the	